IN THE CLAIMS:

Cancel claims 4-6 without prejudice or admission as shown in the following listing of claims, which replaces all previous listings and versions of claims.

1. (canceled).

2. (previously presented) A method of manufacturing a semiconductor integrated circuit in which a CMOS transistor is formed on a first conductivity type semiconductor film provided on a first conductivity type supporting substrate through an embedded insulating film, comprising the steps of:

conducting thermal oxidation to form a LOCOS for element separation between transistors in the semiconductor film;

forming a gate oxide film of a second conductivity type transistor;

forming a first conductivity type impurity region between the gate oxide film and the embedded insulating film in a region where the second conductivity type transistor is to be formed;

forming a polysilicon film on the gate oxide film and etching the polysilicon film so as to form a gate electrode of the second conductivity type transistor;

forming a second conductivity type impurity region in an ultra-shallow portion of each of a source region and a drain region;

forming a second conductivity type impurity region having a low density in a middle portion of each of the source region and the drain region;

forming a second conductivity type impurity region having the same density as the second conductivity type impurity region in the ultra-shallow portion in a lower portion of each of the source region and the drain region; and

providing resist as a mask on a part of the source region and the drain region adjacent to the gate electrode, and further performing ion implantation so as to form a second conductivity type impurity region in each of the source region and the drain region.

3. (previously presented) A method of manufacturing a semiconductor integrated circuit in which a CMOS transistor is formed on a first conductivity type semiconductor film provided on a first conductivity type supporting substrate through an embedded insulating film, comprising the steps of:

conducting thermal oxidation to form a LOCOS for element separation between transistors in the semiconductor film;

forming a gate oxide film of a second conductivity type transistor;

forming a first conductivity type impurity region between the gate oxide film and the embedded insulating film in a region where the second conductivity type transistor is to be formed;

forming a first conductivity type impurity region having a higher density than that of the first conductivity type impurity region in a middle depth portion of the semiconductor film serving as the proximal region to a drain in the first conductivity type impurity region;

forming a polysilicon film on the gate oxide film and etching the polysilicon film so as to form a gate electrode of the second conductivity type transistor; and

performing ion implantation through the gate electrode so as to form a second conductivity type impurity region in each of a source region and a drain region.

4.- 6. (canceled)